

PROCESSING METHOD, METHOD OF MANUFACTURING SEMICONDUCTOR
DEVICE, PROCESSING APPARATUS, AND PROGRAM

ABSTRACT

There is provided a technique that includes: (a) providing a substrate including a first surface and a second surface whose material is different from a material of the first surface, a first oxide film being formed on the first surface, and a second oxide film being formed on the second surface; and (b) removing the second oxide film formed on the second surface while leaving the first oxide film formed on the first surface by exposing the substrate to an etching agent.

Fig. 4D